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**TPS22908** 

SLVSBI7C -JULY 2012-REVISED APRIL 2015

Support &

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# TPS22908 3.6-V, 1-A, 28-mΩ On-Resistance Load Switch with Controlled Rise Time

Technical

Documents

#### 1 Features

- Integrated P-Channel Load Switch
- Input Voltage: 1 V to 3.6 V
- 1 A Maximum Continuous Switch Current
- **On-Resistance (Typical Values)** 
  - R<sub>ON</sub> = 28 m $\Omega$  at V<sub>IN</sub> = 3.6 V
  - R<sub>ON</sub> = 33 mΩ at V<sub>IN</sub> = 2.5 V
  - R<sub>ON</sub> = 42 m $\Omega$  at V<sub>IN</sub> = 1.8 V
  - R<sub>ON</sub> = 70 m $\Omega$  at V<sub>IN</sub> = 1.2 V
- Maximum Quiescent Current = 1 µA
- Maximum Shutdown Current =  $1 \mu A$
- Low Control Input Thresholds Enable Use of 1.2-V, 1.8-V, 2.5-V, and 3.3-V Logic
- Controlled Slew Rate to Avoid Inrush Currents - t<sub>R</sub> = 105 µs at V<sub>IN</sub> = 3.6V
- Four Terminal Wafer-Chip-Scale Package (WCSP)
  - Nominal Dimensions See Addendum for Details
  - 0.9 mm × 0.9 mm, 0.5-mm Pitch, 0.6-mm Height
- Quick Output Discharge (QOD)

### 2 Applications

Tools &

Software

- **Battery Powered Equipment**
- Portable Industrial Equipment
- Portable Medical Equipment
- **Portable Media Players**
- Point of Sale Terminal
- **GPS** Devices
- **Digital Cameras**
- Portable Instrumentation
- Smartphones and Tablets

### 3 Description

The TPS22908 is a small, low RON load switch with controlled turn on. The device contains a P-channel MOSFET that operates over an input voltage range of 1 V to 3.6 V. The switch is controlled by an on/off input (ON), which is capable of interfacing directly with low-voltage control signals.

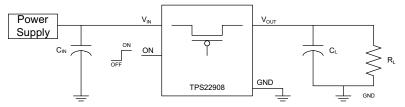
The TPS22908 is available in a space-saving 4terminal WCSP with 0.5 mm pitch (YZT). The device is characterized for operation over the free-air temperature range of -40°C to 85°C.

#### Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)				
TPS22908	DSBGA (4)	0.9mm x 0.9mm				

(1) For all available packages, see the orderable addendum at the end of the datasheet.

### **Typical Application**





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### **4** Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision B (May 2013) to Revision C Page   • Added Pin Configuration and Functions section, ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section Page		
•	Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device	1
Ch	nanges from Revision A (August 2012) to Revision B	Page
•	Updated FEATURES	1

Added Layout graphic...... 16

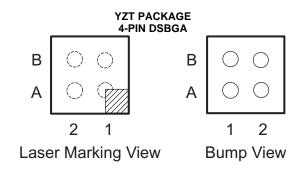


### 5 Device Options

FEATURE	VALUE
Device	TPS22908
R <sub>ON</sub> (Typical) VIN = 3.6 V	28 mΩ
Rise Time (Typical) VIN = 3.6 V	105 µs
Quick Output Discharge <sup>(1)</sup>	Yes
Maximum Current	1 A
Enable	Active high

(1) This feature discharges the output of the switch to ground through an 80- $\Omega$  resistor, preventing the output from floating.

### 6 Pin Configuration and Functions



#### **Pin Functions**

PIN	PIN I/O		DESCRIPTION		
NO.	NAME	1/0	DESCRIPTION		
A1	V <sub>OUT</sub>	0	Switch Output		
A2	V <sub>IN</sub>	I	Switch input, bypass capacitor recommended for minimizing V <sub>IN</sub> dip. See Application Information.		
B1	GND	—	Ground		
B2	ON	I	Switch control input, active high. Do not leave floating.		

### 7 Specifications

### 7.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT <sup>(2)</sup>
V <sub>IN</sub>	Supply voltage	-0.3	4	V
V <sub>OUT</sub>	Output voltage	-0.3	(V <sub>IN</sub> + 0.3)	V
V <sub>ON</sub>	Input voltage	-0.3	4	V
	Maximum Continuous Switch Current for $V_{IN} \ge 1.2 V$		1	^
IMAX	Maximum Continuous Switch Current at V <sub>IN</sub> = 1 V		0.6	A
TJ	Maximum junction temperature <sup>(3)</sup>		125	°C
T <sub>LEAD</sub>	Maximum lead temperature (10-s soldering time)		300	°C
T <sub>STG</sub>	Storage temperature	-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values are with respect to network ground terminal.

(3) In applications where high power dissipation and/or poor package thermal resistance is present, the maximum ambient temperature may have to be derated. Maximum ambient temperature [TA(max)] is dependent on the maximum operating junction temperature [T<sub>J(max)</sub>], the maximum power dissipation of the device in the application [P<sub>D(max)</sub>], and the junction-to-ambient thermal resistance of the part/package in the application (R<sub>0JA</sub>), as given by the following equation: T<sub>A(max)</sub> = T<sub>J(max)</sub> - (R<sub>0JA</sub> × P<sub>D(max)</sub>)

### 7.2 ESD Ratings

			VALUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±2000	
V <sub>(ES</sub>	D) Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22- $\rm C101^{(2)}$	±1000	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

#### 7.3 Recommended Operating Conditions

		MIN	MAX	UNIT
V <sub>IN</sub>	Input voltage	1	3.6	V
V <sub>ON</sub>	ON voltage	0	3.6	V
V <sub>OUT</sub>	Output voltage	0	V <sub>IN</sub>	V
VIH	High-level input voltage, ON	0.85	3.6	V
V <sub>IL</sub>	Low-level input voltage, ON	0	0.4	V
T <sub>A</sub>	Operating free-air temperature range	-40	85	°C
CIN	Input capacitor	1 <sup>(1)</sup>		μF

(1) Refer to application section.

### 7.4 Thermal Information

		TPS22908	
	THERMAL METRIC <sup>(1)</sup>	YZT (DSBGA)	UNIT
		4 PINS	
$R_{ extsf{ heta}JA}$	Junction-to-ambient thermal resistance	188	
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	2	
$R_{\theta JB}$	Junction-to-board thermal resistance	33	°C/W
$\Psi_{JT}$	Junction-to-top characterization parameter	9.1	
Ψ <sub>JB</sub>	Junction-to-board characterization parameter	33	

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

### 7.5 Electrical Characteristics

Unless otherwise noted the specification applies over the operating ambient temp  $-40^{\circ}C \le T_A \le 85^{\circ}C$ . Typical values are for  $V_{IN} = 3.6 \text{ V}$ , and  $T_A = 25^{\circ}C$  unless otherwise noted.

	PARAMETER	TEST CONI	DITIONS	T <sub>A</sub>	MIN TYP	MAX	UNIT
POWER	SUPPLIES AND CURRENTS	<u>.</u>					
I <sub>IN</sub>	Quiescent current	$I_{OUT} = 0 \text{ mA}, V_{IN} = V_{C}$	DN	Full	0.19	1	μA
I <sub>IN(OFF)</sub>	OFF-state supply current	$V_{ON} = 0 V, V_{OUT} = Op$	ben	Full	0.12	1	μA
IIN(LEAK)	OFF-state supply current	$V_{ON} = 0 V, V_{OUT} = 0 V$	V	Full	0.12	1	μA
I <sub>ON</sub>	ON pin input leakage current	V <sub>ON</sub> = 1.1 V to 3.6 V		Full	0.01	0.1	μA
RESISTA	ANCE AND SWITCH CHARACTER	ISTICS				Ľ	
			25°C	28.2	32.1		
			V <sub>IN</sub> = 3.6 V	Full		34.9	mΩ
		V <sub>IN</sub> = 2.5 V 25°C Full	N 0.5.V	25°C	33.1	37.5	
				40.6	mΩ		
<b>D</b>		000 1	N 4.0.V	25°C	41.5	50.3	mΩ
R <sub>ON</sub>	ON-state resistance	I <sub>OUT</sub> = -200 mA	V <sub>IN</sub> = 1.8 V	Full		54.0	
			N 4.0.V	25°C	69.7	87.3	
		V <sub>IN</sub> = 1.2 V	Full		91.2	mΩ	
			N 4.0.V	25°C	112	155	
			V <sub>IN</sub> = 1.0 V	Full		156	mΩ
R <sub>PD</sub>	Output pulldown resistance	V <sub>IN</sub> = 3.3 V, V <sub>ON</sub> = 0 V	V, I <sub>OUT</sub> = 30 mA	25°C	80	100	Ω

### 7.6 Switching Characteristics

	DADAMETED	TEAT CONDITION	TPS22908			
	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT
$V_{IN} = 3$	3.6 V, T <sub>A</sub> = 25°C (unless otherwise noted)					
t <sub>ON</sub>	Turn-ON time	$R_L = 10 \ \Omega, \ C_L = 0.1 \ \mu F$		110		
t <sub>OFF</sub>	Turn-OFF time	$R_L = 10 \ \Omega, \ C_L = 0.1 \ \mu F$		5		
t <sub>R</sub>	V <sub>OUT</sub> Rise time	$R_L = 10 \Omega, C_L = 0.1 \mu F$		105		μs
t <sub>F</sub>	V <sub>OUT</sub> Fall time	$R_L = 10 \ \Omega, \ C_L = 0.1 \ \mu F$		2		
V <sub>IN</sub> = 1	.0 V, T <sub>A</sub> = 25°C (unless otherwise noted)					
t <sub>ON</sub>	Turn-ON time	$R_L = 10 \ \Omega, \ C_L = 0.1 \ \mu F$		493		
t <sub>OFF</sub>	Turn-OFF time	$R_L = 10 \ \Omega, \ C_L = 0.1 \ \mu F$		7		
t <sub>R</sub>	V <sub>OUT</sub> Rise time	$R_L = 10 \Omega, C_L = 0.1 \mu F$		442		μs
t <sub>F</sub>	V <sub>OUT</sub> Fall time	$R_L = 10 \ \Omega, \ C_L = 0.1 \ \mu F$		2		

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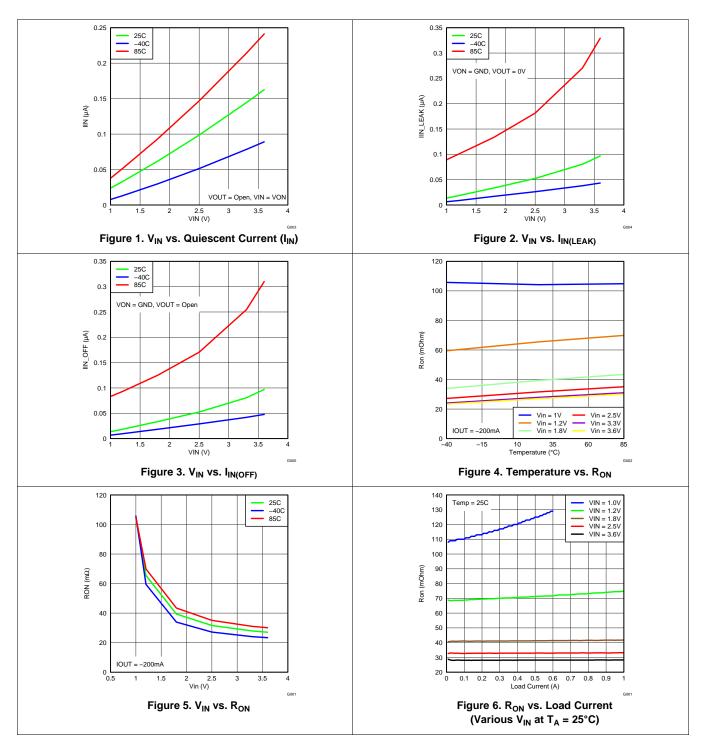
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NSTRUMENTS

Texas

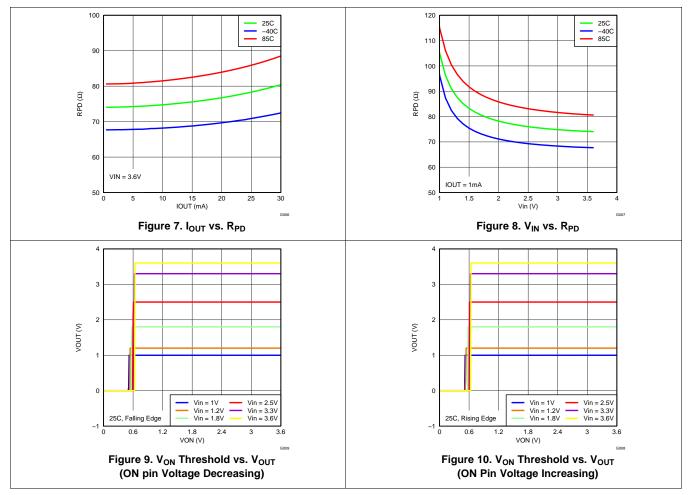
### 7.7 Typical Characteristics

#### 7.7.1 Typical DC Characteristics

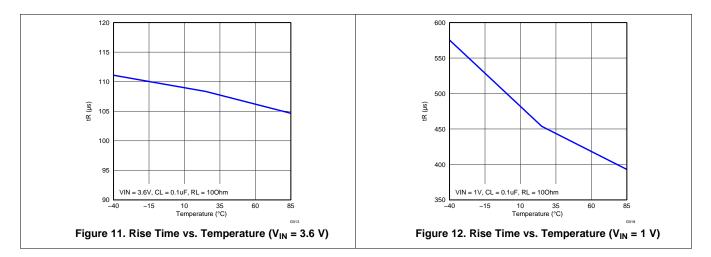




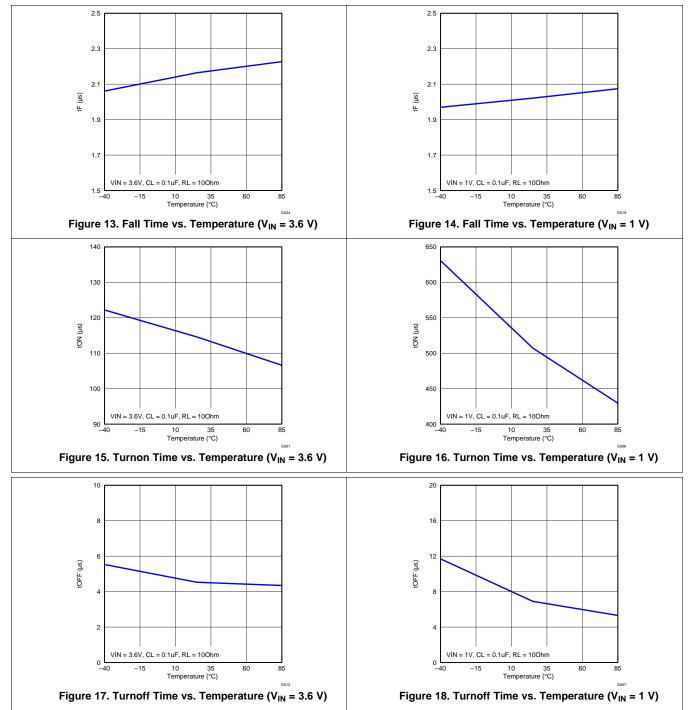
#### **Typical DC Characteristics (continued)**



#### 7.7.2 Typical Switching Characteristics

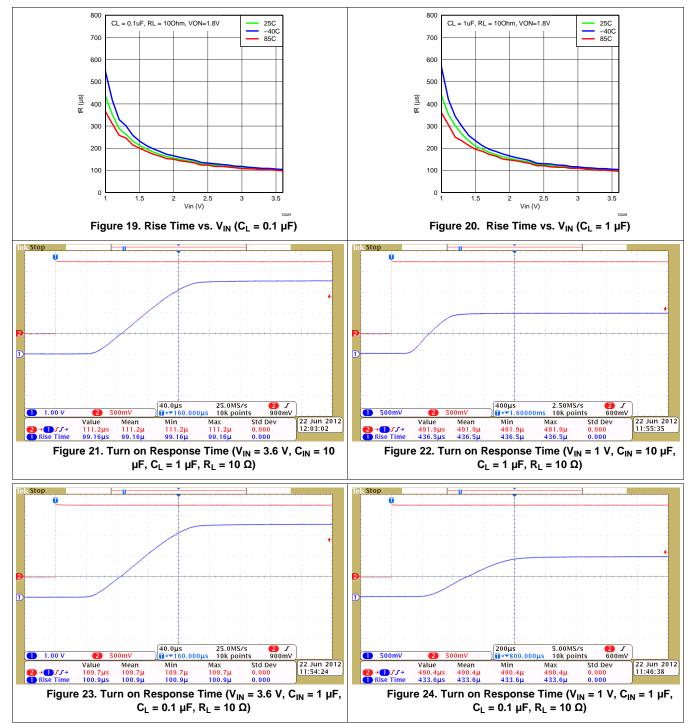


### **Typical Switching Characteristics (continued)**





### **Typical Switching Characteristics (continued)**

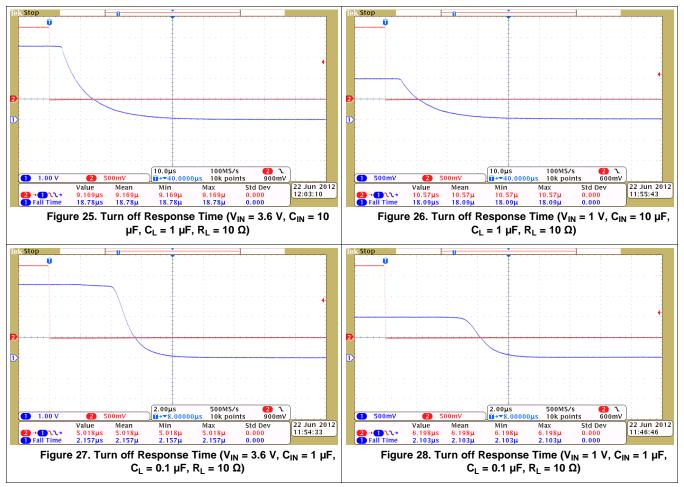


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### **Typical Switching Characteristics (continued)**

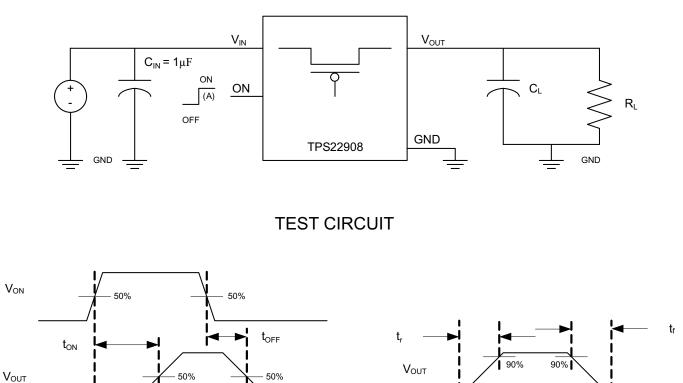




10%

10%

## 8 Parameter Measurement Information





A. Rise and fall times of the control signal is 100 ns.

Figure 29. Test Circuit and  $t_{ON}/t_{OFF}$  Waveforms

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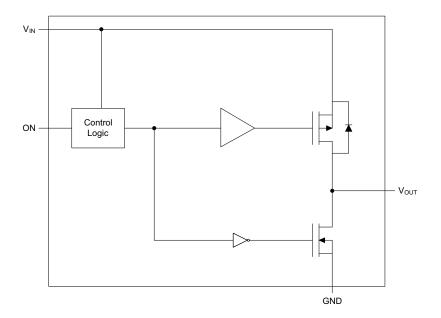


### 9 Detailed Description

#### 9.1 Overview

The TPS22908 is a single channel, 1 A load switch in a small, space-saving DSBGA-4 package. This device implements a P-channel MOSFET to provide a low on-resistance for a low voltage drop across the device. A controlled rise time is used in applications to limit the inrush current.

#### 9.2 Functional Block Diagram



#### 9.3 Feature Description

#### 9.3.1 ON/OFF Control

The ON pin controls the state of the switch. Activating ON continuously holds the switch in the on state. ON is active high and has a low threshold making it capable of interfacing with low-voltage signals. The ON pin is compatible with standard GPIO logic threshold, and it can be used with any microcontroller with 1.2-V, 1.8-V, 2.5-V or 3.3-V GPIOs.

#### 9.3.2 Quick Output Discharge

The TPS22908 includes the Quick Output Discharge (QOD) feature. When the switch is disabled, a discharge resistance with a typical value of 80  $\Omega$  is connected between the output and ground. This resistance pulls down the output and prevents it from floating when the device is disabled.

#### 9.4 Device Functional Modes

ON	V <sub>IN</sub> to V <sub>OUT</sub>	V <sub>OUT</sub> to GND
L	OFF	ON
Н	ON	OFF

#### Table 1. Functional Table



### **10** Application and Implementation

#### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

#### **10.1** Application Information

#### **10.1.1** Input Capacitor (Optional)

To limit the voltage drop on the input supply caused by transient inrush currents when the switch turns on into a discharged load capacitor, a capacitor can be placed between  $V_{IN}$  and GND. A 1  $\mu$ F ceramic capacitor,  $C_{IN}$ , placed close to the pins, is usually sufficient. Higher values of  $C_{IN}$  can be used to further reduce the voltage drop during high-current application. When switching heavy loads, it is recommended to have an input capacitor about 10 times higher than the output capacitor to avoid excessive voltage drop.

#### **10.1.2 Output Capacitor (Optional)**

Due to the integrated body diode of the PMOS switch, a  $C_{IN}$  greater than  $C_L$  is highly recommended. A  $C_L$  greater than  $C_{IN}$  can cause  $V_{OUT}$  to exceed  $V_{IN}$  when the system supply is removed. This could result in current flow through the body diode from  $V_{OUT}$  to  $V_{IN}$ . A  $C_{IN}$  to  $C_L$  ratio of at least 10 to 1 is recommended for minimizing  $V_{IN}$  dip caused by inrush currents during startup; however, a 10 to 1 ratio for capacitance is not required for proper functionality of the device. A ratio smaller than 10 to 1 (such as 1 to 1) could cause slightly more  $V_{IN}$  dip at turn on due to inrush currents.

#### **10.2 Typical Application**

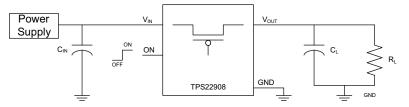


Figure 30. Typical Application Schematic

#### 10.2.1 Design Requirements

The following input parameters will be used in these design examples.

-								
DESIGN PARAMETER	EXAMPLE VALUE							
V <sub>IN</sub>	1.8 V							
CL	10 µF							
Load current	500 mA							
Ambient Temperature	25 °C							
Maximum inrush current	200 mA							

#### **Table 2. Design Parameters**

#### 10.2.2 Detailed Design Procedure

#### 10.2.2.1 Managing Inrush Current

When the switch is enabled, the output capacitors must be charged up from 0 V to the set value (1.8 V in this example). This charge arrives in the form of inrush current. Inrush current can be calculated using Equation 1:

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 $I_{INRUSH} = C_L \times \frac{dV_{OUT}}{dt}$ 

where:

- C<sub>L</sub> = Output capacitance
- dV<sub>OUT</sub> = Output voltage
- dt = Rise time

The TPS22908 offers a controlled rise time for minimizing inrush current. This device can be selected based upon the minimum acceptable rise time which can be calculated using the design requirements and the inrush current equation. An output capacitance of 4.7  $\mu$ F will be used since the amount of inrush current increases with output capacitance:

$$200 \text{ mA} = 10 \ \mu\text{F} \times 1.8 \text{V} / \text{dt}$$

dt = 90 µs

To ensure an inrush current of less than 200 mA, a device with a rise time greater than 90  $\mu$ s must be used. The TPS22908 has a typical rise time of 160  $\mu$ s at 1.8 V which meets the above design requirements.

#### 10.2.2.2 VIN to VOUT Voltage Drop

The voltage drop from VIN to VOUT is determined by the ON-resistance of the device and the load current.  $R_{ON}$  can be found in *Electrical Characteristics* and is dependent on temperature. When the value of  $R_{ON}$  is found, the following equation can be used to calculate the voltage drop across the device:

 $\Delta V = I_{LOAD} \times R_{ON}$ 

where:

- $\Delta V = Voltage drop across the device$
- I<sub>LOAD</sub> = Load current
- R<sub>ON</sub> = ON-resistance of the device

At  $V_{IN}$  = 1.8 V, the TPS22908 has an R<sub>ON</sub> value of 42 m $\Omega$ . Using this value and the defined load current, the above equation can be evaluated:

 $\Delta V = 500 \text{ mA} \times 42 \text{ m}\Omega$ 

$$\Delta V = 21 \text{ mV}$$
  
Therefore, the voltage drop across the device will be 21 mV.

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(1)

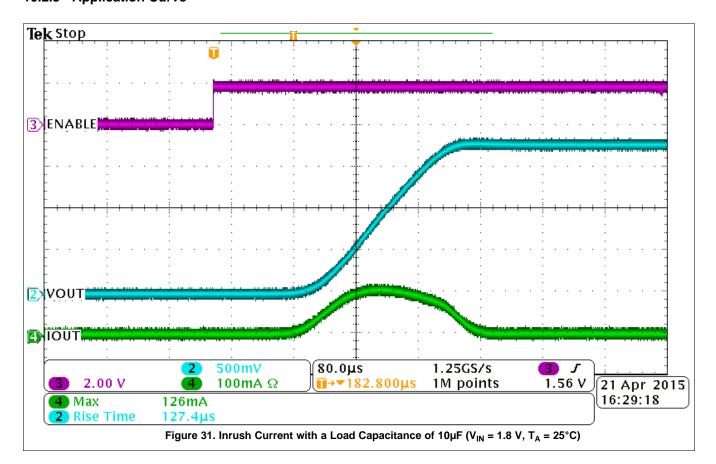
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(3)





### **11 Power Supply Recommendations**

The device is designed to operate with a VIN range of 1 V to 3.6 V. This supply must be well regulated and placed as close to the device terminals as possible. It must also be able to withstand all transient and load currents, using a recommended input capacitance of 1  $\mu$ F if necessary. If the supply is located more than a few inches from the device terminals, additional bulk capacitance may be required in addition to the ceramic bypass capacitors. If additional bulk capacitance is required, an electrolytic, tantalum, or ceramic capacitor of 10  $\mu$ F may be sufficient.

### 12 Layout

### 12.1 Layout Guidelines

For best performance, VIN, VOUT, and GND traces should be as short and wide as possible to help minimize the parasitic electrical effects. To be most effective, the input and output capacitors should be placed close to the device to minimize the effects that parasitic trace inductances may have on normal operation.

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#### 12.2 Layout Example

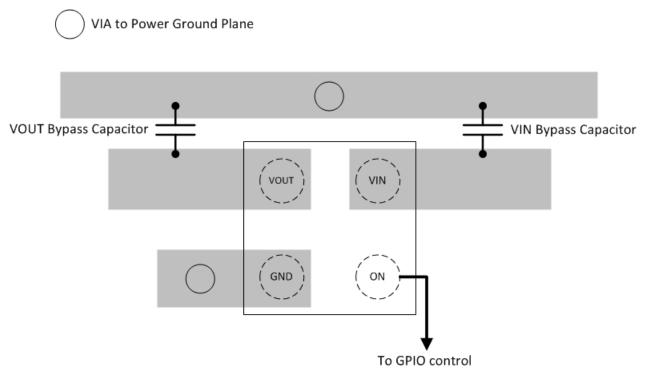


Figure 32. Layout Example

### 12.3 Thermal Considerations

For higher reliability, the maximum IC junction temperature,  $T_{J(max)}$ , should be restricted to 125°C under normal operating conditions. Junction temperature is directly proportional to power dissipation in the device and the two are related by:

 $T_J = T_A + R_{\theta JA} \times P_D$ 

where:

- T<sub>J</sub> = Junction temperature of the device
- T<sub>A</sub> = Ambient temperature
- P<sub>D</sub> = Power dissipation inside the device
- R<sub>0JA</sub> = Junction to ambient thermal resistance. See *Thermal Information* for more information. This parameter is highly dependent on board layout. (5)



### **13** Device and Documentation Support

### 13.1 Trademarks

All trademarks are the property of their respective owners.

#### **13.2 Electrostatic Discharge Caution**



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### 13.3 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

### 14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



21-Feb-2015

### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
TPS22908YZTR	ACTIVE	DSBGA	YZT	4	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	AT	Samples
TPS22908YZTT	ACTIVE	DSBGA	YZT	4	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(AT ~ ATF)	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW**: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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## PACKAGE MATERIALS INFORMATION

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### TAPE AND REEL INFORMATION





## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS22908YZTR	DSBGA	YZT	4	3000	180.0	8.4	0.99	0.99	0.69	4.0	8.0	Q1
TPS22908YZTR	DSBGA	YZT	4	3000	178.0	9.2	1.0	1.0	0.73	4.0	8.0	Q1
TPS22908YZTT	DSBGA	YZT	4	250	180.0	8.4	0.99	0.99	0.69	4.0	8.0	Q1

TEXAS INSTRUMENTS

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## PACKAGE MATERIALS INFORMATION

17-Jun-2015

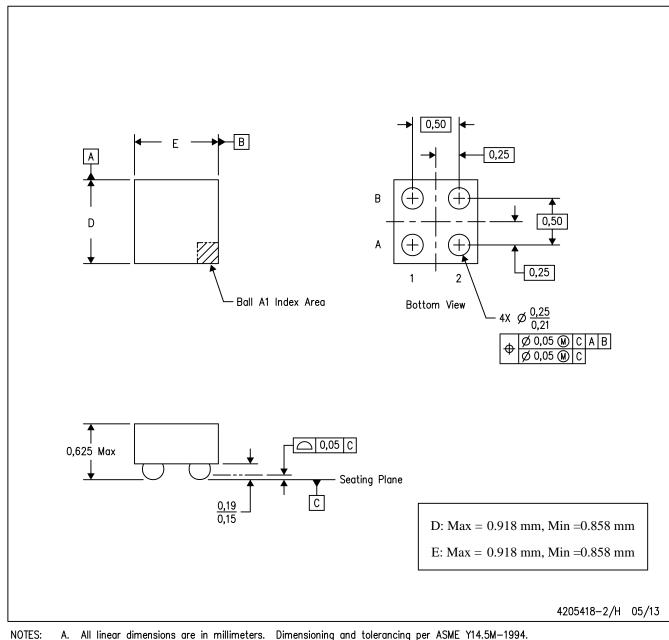


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS22908YZTR	DSBGA	YZT	4	3000	182.0	182.0	20.0
TPS22908YZTR	DSBGA	YZT	4	3000	220.0	220.0	35.0
TPS22908YZTT	DSBGA	YZT	4	250	182.0	182.0	20.0

YZT (S-XBGA-N4)

DIE-SIZE BALL GRID ARRAY



- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.

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